SUNDAY, March 26, TUTORIALS 8a.m.-5:00 p.m.

<table>
<tr>
<td rowspan="2">101.
Reliability definitions and basic concepts
R. Degraeve (IMEC)
(8:00-11:30 a.m.)</td>
<td>121.
SER fundamentals
N. Seifert (Intel)
(8:00-9:30 a.m.)</td>
<td>151.
Analog and digital circuits
K. Roy (Purdue)
(8:00-9:30 a.m.)</td>
<td>170.
FeRam reliability
J. Rodriguez (TI)
(8:00-9:30 a.m.)</td>
</tr>
<tr>
<td>122.
Soft error detection and mitigation in computer system
C. Slayman (Sun Micro)
(10:00-11:30 a.m.)</td>
<td>152.
Mixed signal circuit reliability from device stress conditions to IC-failure
C. Schluender (Infineon)
(10:00-11:30 a.m.)</td>
<td>180.
Hydrogen in Si
S. Ashok (Penn State)
(10:00-11:30 a.m.)</td>
</tr>
<tr>
<td>102.
Fast wafer level reliability monitoring fWLR
A. Martin (Infineon)
(1:30-3:00 p.m.)</td>
<td>130.
Advanced interconnect processes for the 45nm node and beyond
J. Gambino (IBM)
(1:30-3:00 p.m.)</td>
<td>160.
ESD and latchup
G. Boselli (TI)
(1:30-3:00 p.m.)</td>
<td>191.
NBTI:
A simple view of a complex phenomena
A. Alam (Purdue)
(1:30-3:00 p.m.)</td>
</tr>
<tr>
<td>110.
Process induced damage – a history and prognosis
T. Hook (IBM)
3:30-5:00 p.m.</td>
<td>140.
Physics of silicon package interactions with special regard to reliability
K. Seshan (Intel)
3:30-5:00 p.m.</td>
<td></td>
<td>192.
Electrical characterization and modeling of NBTI in p-MOSFET devices
S. Mahapatra (IIT Bombay)
3:30-5:00 p.m.</td>
</tr>
</table>